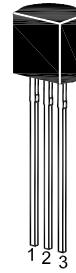


BC369

PNP Silicon Epitaxial Planar Transistor

Applications

- General purpose switching and amplification
- Power application such as audio output stages



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	32	V
Collector Emitter Voltage	$-V_{CEO}$	20	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current (DC)	$-I_C$	1	A
Peak Collector Current	$-I_{CM}$	2	A
Total Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 10\text{ V}$, $-I_C = 5\text{ mA}$ at $-V_{CE} = 1\text{ V}$, $-I_C = 500\text{ mA}$ at $-V_{CE} = 1\text{ V}$, $-I_C = 1\text{ A}$	h_{FE} h_{FE} h_{FE}	50 85 60	- 375 -	- - -
Collector Base Cutoff Current at $-V_{CB} = 25\text{ V}$	$-I_{CBO}$	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	32	-	V
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	20	-	V
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C = 1\text{ A}$, $-I_B = 100\text{ mA}$	$-V_{CE(sat)}$	-	0.5	V
Base Emitter On Voltage at $-V_{CE} = 1\text{ V}$, $-I_C = 1\text{ A}$	$-V_{BE(on)}$	-	1	V
Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 20\text{ MHz}$	f_T	40	-	MHz

